

### 2SA1611 TRANSISTOR (PNP)

#### FEATURES

Power dissipation

$$P_{CM} : 0.15 \text{ W (Tamb=25}^\circ\text{C)}$$

Collector current

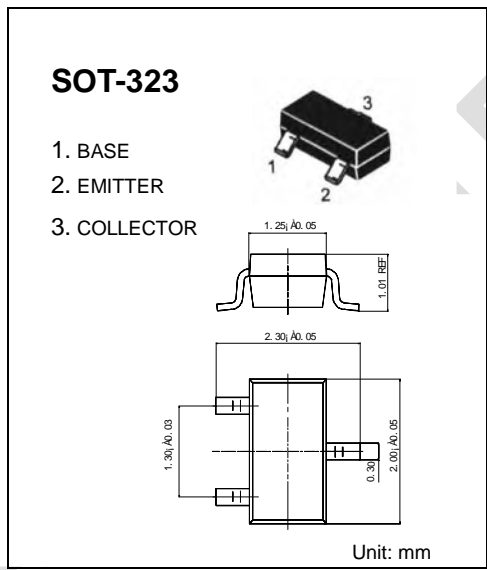
$$I_{CM} : -0.1 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : -60 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$



#### ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}, I_E=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-60\text{V}, I_E=0$			-0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-5\text{V}, I_C=0$			-0.1	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE}=-6\text{V}, I_C=-1\text{mA}$	90		600	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100\text{mA}, I_B=-10\text{mA}$			-0.3	V
Base-emitter voltage	$V_{BE}$	$V_{CE}=-6\text{V}, I_C=-1\text{mA}$	-0.58		-0.68	V
Transition frequency	$f_T$	$V_{CE}=-6\text{V}, I_C=-10\text{mA}$		180		MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		4.5		pF

#### CLASSIFICATION OF $h_{FE(1)}$

Rank	M4	M5	M6	M7
Range	90-180	135-270	200-400	300-600
Marking	M4	M5	M6	M7

### Typical Characteristics

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